

PNP TIP115-116-117

SILICON DARLINGTON POWER TRANSISTORS

PNP epitaxial-base transistors in a monolithic Darlington circuit and housed in a TO-220 envelope. They are designed for general purpose amplifier and low-speed switching applications.

NPN complements are TIP110-111-112

Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit	
V_{CBO}	Collector-Base Voltage		TIP110	-60	V
			TIP111	-80	
			TIP112	-100	
V_{CEO}	Collector-Emitter Voltage		TIP110	-60	V
			TIP111	-80	
			TIP112	-100	
V_{EBO}	Emitter-Base Voltage		TIP110	-5	V
			TIP111		
			TIP112		
I_C	Collector Current		TIP110	-2	A
			TIP111		
			TIP112		
I_{CM}	Collector Peak Current		TIP110	-4	A
			TIP111		
			TIP112		
I_B	Base Current		TIP110	50	mA
			TIP111		
			TIP112		
P_T	Power Dissipation	@ $T_c < 25^\circ$	TIP110	50	Watts
			TIP111		
			TIP112		
		@ $T_a < 25^\circ$	TIP110	2	
			TIP111		
			TIP112		
T_J	Junction Temperature		TIP110	150	$^{\circ}\text{C}$
			TIP111		
			TIP112		
T_s	Storage Temperature range		TIP110	-65 to +150	
			TIP111		
			TIP112		

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THERMAL CHARACTERISTICS

Symbol	Ratings		Value	Unit
$R_{thJ-case}$	From junction-case	TIP110	2.5	°C/W
		TIP111		
		TIP112		
$R_{thJ-amb}$	From junction-ambient	TIP110	62.5	°C/W
		TIP111		
		TIP112		

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

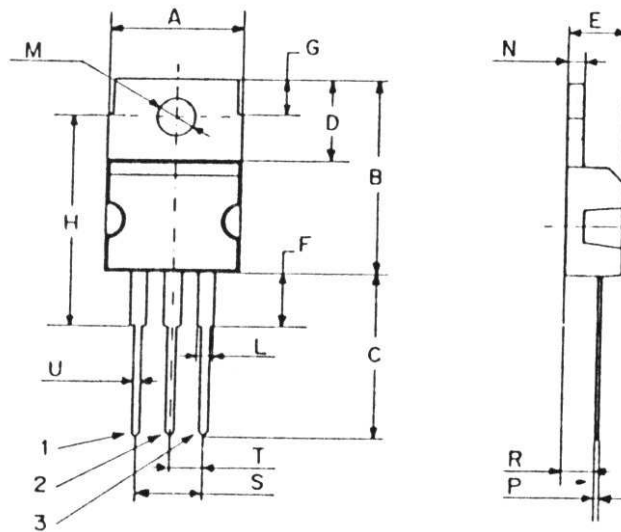
Symbol	Ratings	Test Condition(s)		Min	Typ	Max	Unit
I _{CBO}	Collector Cutoff Current	I _E = 0,V _{CB} = -V _{CBO} max	TIP110	-	-	-1	mA
			TIP111				
			TIP112				
I _{CEO}	Collector Cutoff Current	I _E = 0, V _{CE} = -1/2 V _{CEO} max	TIP110	-	-	-2	mA
			TIP111				
			TIP112				
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5 V, I _C = 0	TIP110	-	-	-2	mA
			TIP111				
			TIP112				
V _{CEO}	Collector-Emitter Breakdown Voltage (*)	I _C = -30 mA, I _B = 0	TIP110	-60	-	-	V
			TIP111	-80	-	-	
			TIP112	-100	-	-	
V _{CE(SAT)}	Collector-Emitter saturation Voltage (*)	I _C = -2 A, I _B = -8 mA	TIP110	-	-	-2.5	V
			TIP111				
			TIP112				
V _{BE(on)}	Base-Emitter Voltage (*)	I _C = -2 A, V _{CE} = -4 V	TIP110	-	-	-2.8	V
			TIP111				
			TIP112				
h _{FE}	DC Current Gain (*)	V _{CE} = -4 V, I _C = -1 A	TIP110	1000	-	-	-
			TIP111				
			TIP112				
		V _{CE} = -4 V, I _C = -2 A	TIP110	500	-	-	
			TIP111				
			TIP112				
C _{OB}	Output Capacitance	I _E = 0, V _{CB} = -10 V f= 0.1MHZ	TIP110	-	-	200	pF
			TIP111				
			TIP112				

(*) Pulse Width $\approx 300 \mu s$, Duty Cycle $\angle 2.0\%$

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MECHANICAL DATA CASE TO-220

DIMENSIONS (mm)		
	Min.	Max.
A	9,90	10,30
B	15,65	15,90
C	13,20	13,40
D	6,45	6,65
E	4,30	4,50
F	2,70	3,15
G	2,60	3,00
H	15,75	17,15
L	1,15	1,40
M	3,50	3,70
N	-	1,37
P	0,46	0,55
R	2,50	2,70
S	4,98	5,08
T	2,49	2,54
U	0,70	0,90



Pin 1 :	Base
Pin 2 :	Collector
Pin 3 :	Emitter
Package	Collector

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